

### **NDT3055L**

# N-Channel Logic Level Enhancement Mode Field Effect Transistor

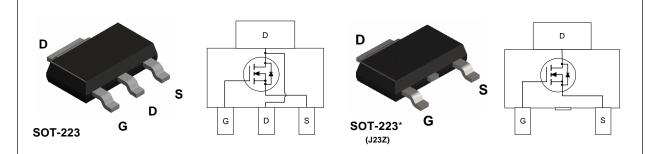
#### **General Description**

These logic level N-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, high cell density, DMOS technology. This very high density process is especially tailored to minimize on-state resistance and provide superior switching performance, and withstand high energy pulse in the avalanche and commutation modes. These devices are particularly suited for low voltage applications such as DC motor control and DC/DC conversion where fast switching, low in-line power loss, and resistance to transients are needed.

#### **Features**

- Low drive requirements allowing operation directly from logic drivers. V<sub>GS(TH)</sub> < 2V.</li>
- High density cell design for extremely low R<sub>DS(ON)</sub>.
- High power and current handling capability in a widely used surface mount package.





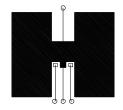
# **Absolute Maximum Ratings** $T_A = 25^{\circ}C$ unless otherwise noted

Symbol	Parameter	NDT3055L	Units	
V <sub>DSS</sub>	Drain-Source Voltage	60	V	
$V_{GSS}$	Gate-Source Voltage - Continuous	±20	V	
D	Maximum Drain Current - Continuous (Note	91a) 4	А	
	- Pulsed	25		
P <sub>D</sub>	Maximum Power Dissipation (Note of	1a) 3	W	
	(Note 1b)	1.3		
	(Note 1c)	1.1		
$\Gamma_{J}$ , $T_{STG}$	Operating and Storage Temperature Range	-65 to 150	.€	
THERMA	L CHARACTERISTICS		·	
R <sub>eJA</sub>	Thermal Resistance, Junction-to-Ambient (Not	te 1a) 42	°C/W	
R <sub>euc</sub>	Thermal Resistance, Junction-to-Case (Not	te 1) 12	°C/W	

<sup>1998</sup> Fairchild Semiconductor Corporation

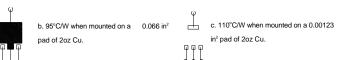
Symbol	Parameter	Conditions				Max	Units
OFF CHAR	RACTERISTICS						
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_{D} = 250 \mu\text{A}$		60			V
$\Delta$ BV <sub>DSS</sub> / $\Delta$ T <sub>J</sub>	Breakdown Voltage Temp. Coefficient	$I_D = 250 \mu\text{A}$ , Referenced to	25 °C		55		mV/°C
DSS	Zero Gate Voltage Drain Current	$V_{DS} = 60 \text{ V}, V_{GS} = 0 \text{ V}$			1	μA	
			T <sub>J</sub> =125°C			50	μA
GSSF	Gate - Body Leakage, Forward	$V_{GS} = 20 \text{ V}, V_{DS} = 0 \text{ V}$				100	nA
GSSR	Gate - Body Leakage, Reverse	$V_{GS} = -20 \text{ V}, V_{DS} = 0 \text{ V}$				-100	nA
	ACTERISTICS (Note 2)						
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu\text{A}$		1	1.6	2	V
$\Delta V_{GS(th)}/\Delta T_{J}$	Gate Threshold Voltage Temp. Coefficient	$I_D = 250 \mu\text{A}$ , Referenced to	25 °C		-4		mV /°C
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance	$V_{GS} = 10 \text{ V}, I_{D} = 4 \text{ A}$			0.07	0.1	Ω
()			T <sub>J</sub> =125°C		0.125	0.18	1
		$V_{GS} = 4.5 \text{ V}, I_D = 3.7 \text{ A}$			0.103	0.12	
D(ON)	On-State Drain Current	$V_{GS} = 5$ , $V_{DS} = 10 \text{ V}$		10			Α
9 <sub>FS</sub>	Forward Transconductance	$V_{DS} = 5 \text{ V}, I_{D} = 4 \text{ A}$			7		S
DYNAMIC (	CHARACTERISTICS						
C <sub>iss</sub>	Input Capacitance		345		pF		
Coss	Output Capacitance	$V_{DS} = 25, V_{GS} = 0 V,$ f = 1.0 MHz		110		pF	
C <sub>rss</sub>	Reverse Transfer Capacitance			30		pF	
SWITCHING	G CHARACTERISTICS (Note 2)						
t <sub>D(on)</sub>	Turn - On Delay Time	$V_{DD} = 25, I_{D} = 1 A,$		5	20	ns	
Tr	Turn - On Rise Time	Turn - On Rise Time $V_{GS}$ = 10 V, $R_{GEN}$ = 6 $\Omega$					ns
D(off)	Turn - Off Delay Time		7			50	ns
f	Turn - Off Fall Time				7	20	ns
Q <sub>g</sub>	Total Gate Charge	$V_{DS} = 40 \text{ V}, I_{D} = 4 \text{ A},$		13	20	nC	
$Q_{gs}$	Gate-Source Charge	V <sub>GS</sub> = 10 V		1.7		nC	
$Q_{gd}$	Gate-Drain Charge			3.2		nC	
DRAIN-SO	URCE DIODE CHARACTERISTICS AND MAX	IMUM RATINGS					
s	Maximum Continuous Drain-Source Diode Fo	orward Current				2.5	Α
V <sub>SD</sub>	Drain-Source Diode Forward Voltage	$V_{GS} = 0 \text{ V}, I_{S} = 2.5 \text{ A}$ (Note	2)		0.8	1.2	V

the drain pins.  $\boldsymbol{R}_{\boldsymbol{\theta}^{JC}}$  is



a. 42°C/W when mounted on a 1 in² pad of 2oz Cu.





Scale 1 : 1 on letter size paper 2. Pulse Test: Pulse Width  $\leq$  300 $\mu$ s, Duty Cycle  $\leq$  2.0%

<sup>1.</sup> R<sub>gut</sub> is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of guaranteed by design while  $\boldsymbol{R}_{\theta \text{CA}}$  is determined by the user's board design.

# **Typical Electrical Characteristics**

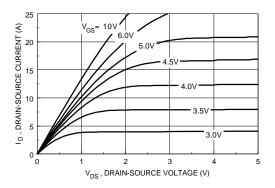


Figure 1. On-Region Characteristics.

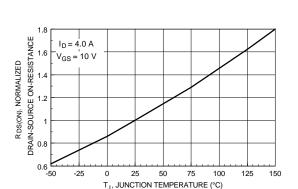


Figure 3. On-Resistance Variation with Temperature.

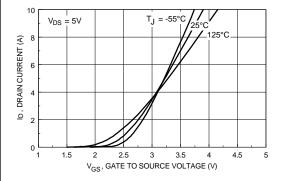


Figure 5. Transfer Characteristics.

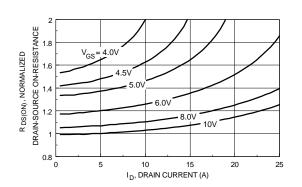


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

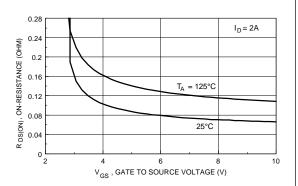


Figure 4. On-Resistance Variation with Gate-to- Source Voltage.

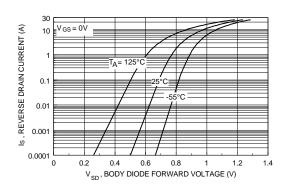


Figure 6. Body Diode Forward Voltage Variation with Current and Temperature.

# **Typical Electrical Characteristics (continued)**

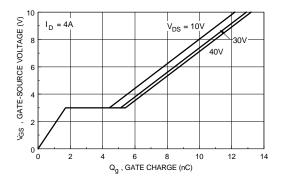


Figure 7. Gate Charge Characteristics.

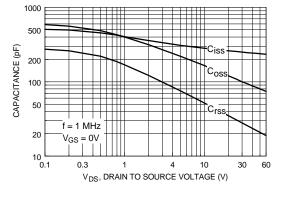
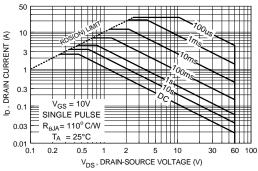


Figure 8. Capacitance Characteristics.

SINGLE PULSE

R<sub>0JA</sub>=110°C/W



00

60

POWER (W)

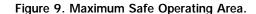
20

0.001

0.01

Figure 10. Single Pulse Maximum Power Dissipation.

SINGLE PULSE TIME (SEC)



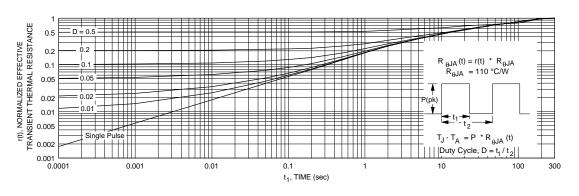
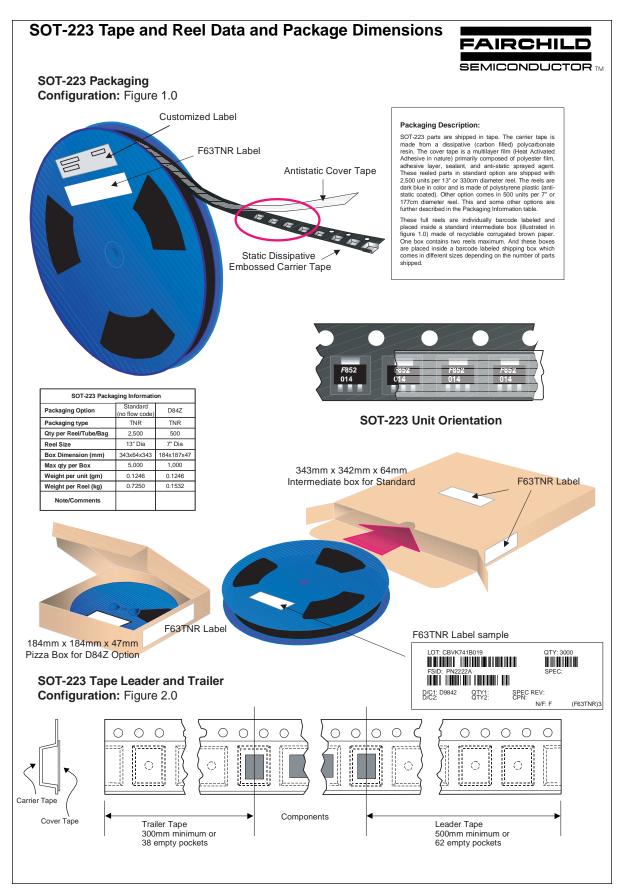


Figure 11. Transient Thermal Response Curve.

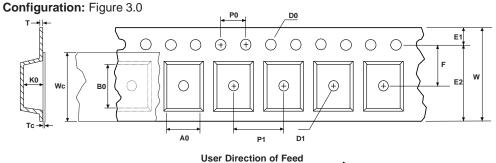
Thermal characterization performed using the conditions described in note 1c.

Transient thermal response will change depending on the circuit board design.





# **SOT-223 Embossed Carrier Tape**

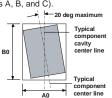


Dimensions are in millimeter														
Pkg type	Α0	В0	w	D0	D1	E1	E2	F	P1	P0	K0	т	Wc	Тс
<b>SOT-223</b> (12mm)	6.83 +/-0.10	7.42 +/-0.10	12.0 +/-0.3	1.55 +/-0.05	1.50 +/-0.10	1.75 +/-0.10	10.25 min	5.50 +/-0.05	8.0 +/-0.1	4.0 +/-0.1	1.88 +/-0.10	0.292 +/- 0.0130	9.5 +/-0.025	0.06 +/-0.02

Notes: A0, B0, and K0 dimensions are determined with respect to the EIA/Jedec RS-481 rotational and lateral movement requirements (see sketches A, B, and C).



Sketch A (Side or Front Sectional View)
Component Rotation

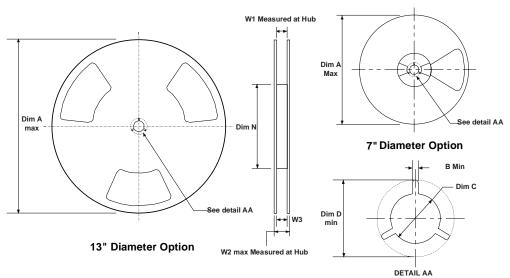


Sketch B (Top View)
Component Rotation



Sketch C (Top View)
Component lateral movement

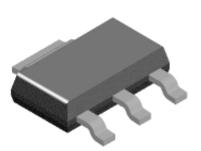
# SOT-223 Reel Configuration: Figure 4.0

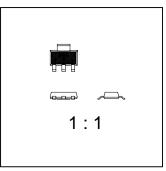


Dimensions are in inches and millimeters									
Tape Size	Reel Option	Dim A	Dim B	Dim C	Dim D	Dim N	Dim W1	Dim W2	Dim W3 (LSL-USL)
12mm	7" Dia	7.00 177.8	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	5.906 150	0.488 +0.078/-0.000 12.4 +2/0	0.724 18.4	0.469 - 0.606 11.9 - 15.4
12mm	13" Dia	13.00 330	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	7.00 178	0.488 +0.078/-0.000 12.4 +2/0	0.724 18.4	0.469 - 0.606 11.9 - 15.4

# SOT-223 Tape and Reel Data and Package Dimensions, continued

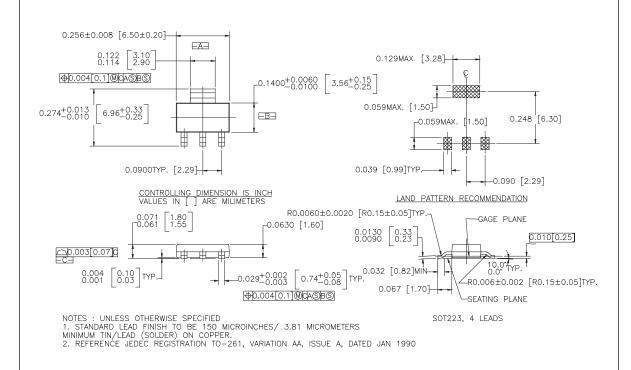
# SOT-223 (FS PKG Code 47)





Scale 1:1 on letter size paper

Part Weight per unit (gram): 0.1246



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